

MSKSEMI

SEMICONDUCTOR



ESD



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PLED

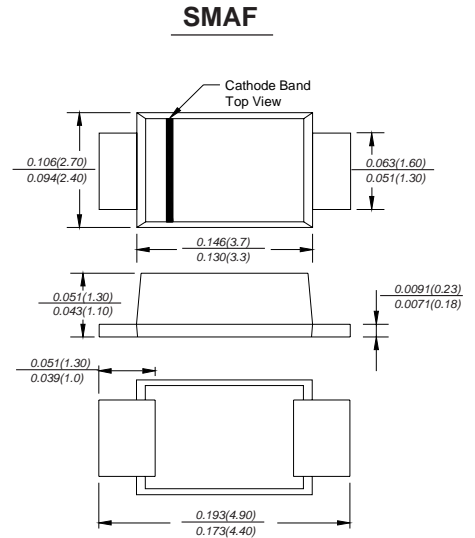
Product data sheet

FEATURES

The plastic package carries Underwriters Laboratory
Flammability Classification 94V-0
For surface mounted applications
Low reverse leakage
Built-in strain relief, ideal for automated placement
High forward surge current capability
High temperature soldering guaranteed:
260°C/10 seconds at terminals
Glass passivated chip junction

MECHANICAL DATA

Case: JEDEC SMAF molded plastic body over passivated chip
Terminals: Solder plated, solderable per MIL-STD-750,
Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.0018 ounce, 0.064 grams



REEL SPECIFICATION

P/N	PKG	QTY
M1F THRU M7F	SMAF	3000

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

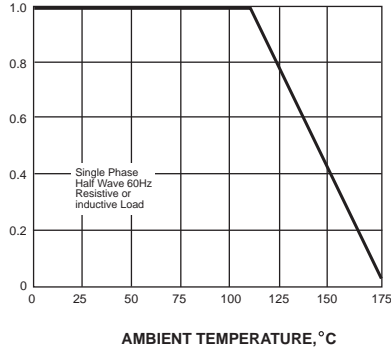
MDD Catalog Number	SYMBOLS	M1F	M2F	M3F	M4F	M5F	M6F	M7F	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at T _L =75°C	I _(AV)	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V _F	1.1							Volts
Maximum DC reverse current at rated DC blocking voltage T _A =25°C T _A =100°C	I _R	5.0 50.0							μA
Typical junction capacitance (NOTE 1)	C _J	15.0							pF
Typical thermal resistance (NOTE 2)	R _{θJA}	75.0							°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-50 to +150							°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES M1F THRU M7F

AVERAGE FORWARD RECTIFIED CURRENT, AMPERES

FIG. 1- FORWARD CURRENT DERATING CURVE



PEAK FORWARD SURGE CURRENT, AMPERES

FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

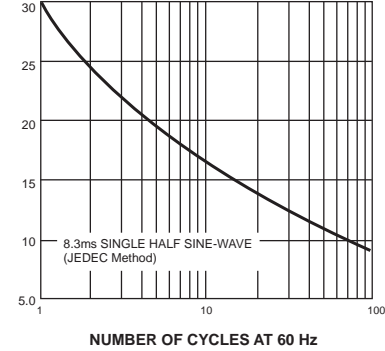


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

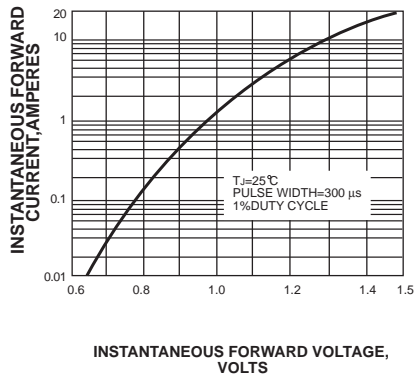


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

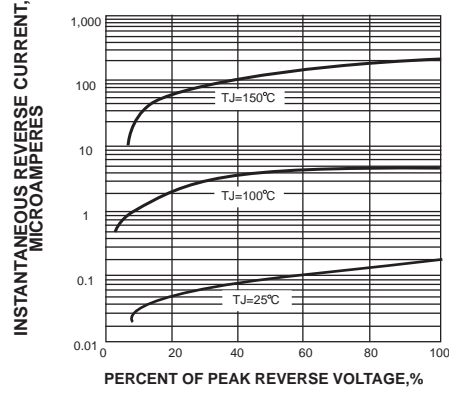


FIG. 5-TYPICAL JUNCTION CAPACITANCE

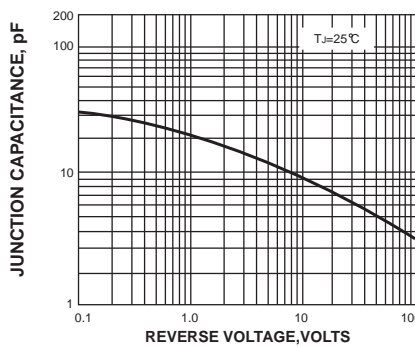
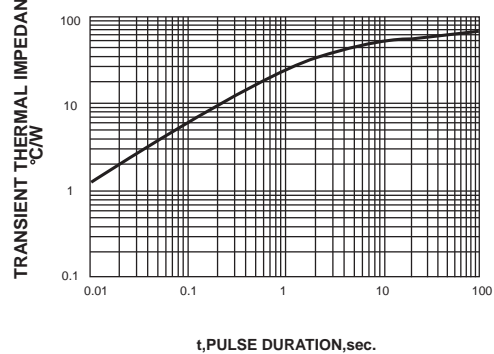


FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE



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